

## Abstract

### **Method for producing semiconductor wafers with epitaxial layer in a chamber of a deposition reactor**

5

Method for producing semiconductor wafers with epitaxial layer in a chamber of a deposition reactor of a plant, comprising  
repeatedly depositing an epitaxial layer on a substrate wafer in the chamber of the  
10 deposition reactor, producing a first number of semiconductor wafers with epitaxial layer, and at the same time  
conditioning a replacement chamber of the deposition reactor outside the plant by purging the replacement chamber with a purge gas;  
interrupting the repeated deposition of an epitaxial layer on a substrate wafer;  
15 replacing the chamber by the replacement chamber; and  
continuing the repeated deposition of an epitaxial layer on a substrate wafer in the replacement chamber of the deposition reactor, producing a second number of semiconductor wafers with epitaxial layer.

20

Drawing for the Abstract: Fig. 1